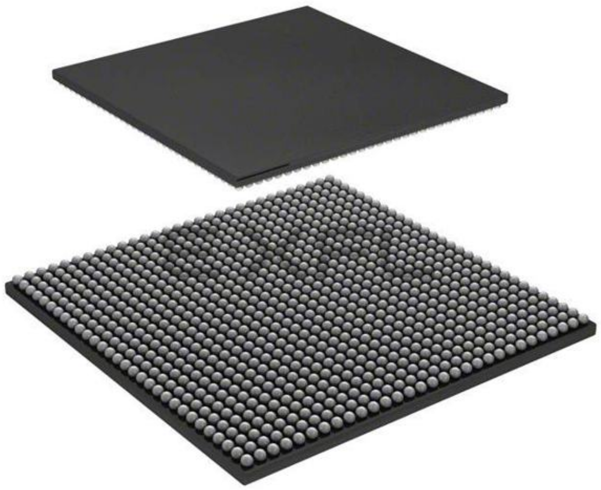
AMD Xilinx - XCZU6CG-2FFVC900E Datasheet



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What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details	
Product Status	Active
Architecture	MCU, FPGA
Core Processor	Dual ARM® Cortex®-A53 MPCore™ with CoreSight™, Dual ARM®Cortex™-R5 with CoreSight™
Flash Size	-
RAM Size	256KB
Peripherals	DMA, WDT
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, MMC/SD/SDIO, SPI, UART/USART, USB OTG
Speed	533MHz, 1.3GHz
Primary Attributes	Zynq®UltraScale+™ FPGA, 469K+ Logic Cells
Operating Temperature	0°C ~ 100°C (TJ)
Package / Case	900-BBGA, FCBGA
Supplier Device Package	900-FCBGA (31x31)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xczu6cg-2ffvc900e

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Table 4: **DC Characteristics Over Recommended Operating Conditions *(Cont'd)***

Symbol	Description	Min	Typ(1)	Max	Units
I_{CC_PSBATT}(4)(5)	Battery supply current at V_{CC_PSBATT} = 1.50V, RTC enabled.	–	–	3650	nA
	Battery supply current at V_{CC_PSBATT} = 1.50V, RTC disabled.	–	–	650	nA
	Battery supply current at V_{CC_PSBATT} = 1.20V, RTC enabled.	–	–	3150	nA
	Battery supply current at V_{CC_PSBATT} = 1.20V, RTC disabled.	–	–	150	nA
I_{PSFS}(6)	PS V_{CC_PSAUX} additional supply current during eFUSE programming.	–	–	115	mA
Calibrated programmable on-die termination (DCI) in HP I/O banks(8) (measured per JEDEC specification)					
R(9)	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_40.	–10%(7)	40	+10%(7)	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_48.	–10%(7)	48	+10%(7)	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_60.	–10%(7)	60	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_40.	–10%(7)	40	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_48.	–10%(7)	48	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_60.	–10%(7)	60	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_120.	–10%(7)	120	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_240.	–10%(7)	240	+10%(7)	Ω
Uncalibrated programmable on-die termination in HP I/Os banks (measured per JEDEC specification)					
R(9)	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_40.	–50%	40	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_48.	–50%	48	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_60.	–50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_40.	–50%	40	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_48.	–50%	48	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_60.	–50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_120.	–50%	120	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_240.	–50%	240	+50%	Ω
Uncalibrated programmable on-die termination in HD I/O banks (measured per JEDEC specification)					
R(9)	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_48.	–50%	48	+50%	Ω
Internal V_{REF}	50% V_{CCO}	V_{CCO} x 0.49	V_{CCO} x 0.50	V_{CCO} x 0.51	V
	70% V_{CCO}	V_{CCO} x 0.69	V_{CCO} x 0.70	V_{CCO} x 0.71	V

Table 4: **DC Characteristics Over Recommended Operating Conditions *(Cont'd)***

Symbol	Description	Min	Typ[1]	Max	Units
Differential termination	Programmable differential termination (TERM_100) for HP I/O banks.	–35%	100	+35%	Ω
n	Temperature diode ideality factor.	–	1.026	–	–
r	Temperature diode series resistance.	–	2	–	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. For HP I/O banks with a V_{CCO} of 1.8V and separated V_{CCO} and V_{CCAUX_IO} power supplies, the I_L maximum current is 70 µA.
3. This measurement represents the die capacitance at the pad, not including the package.
4. Maximum value specified for worst case process at 25°C.
5. I_{CC_PSBATT} is measured when the battery-backed RAM (BBRAM) is enabled.
6. Do not program eFUSE during device configuration (e.g., during configuration, during configuration readback, or when readback CRC is active).
7. If VRP resides at a different bank (DCI cascade), the range increases to ±15%.
8. VRP resistor tolerance is (240Ω ±1%)
9. On-die input termination resistance, for more information see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).

Table 5: **PS MIO Pull-up and Pull-down Current**

Symbol	Description	Min	Max	Units
I_{RPU}	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO_PSMIO} = 3.3V.	20	80	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO_PSMIO} = 2.5V.	20	80	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO_PSMIO} = 1.8V.	15	65	µA
I_{RPD}	Pad pull-down (when selected) at V_{IN} = 3.3V.	20	80	µA
	Pad pull-down (when selected) at V_{IN} = 2.5V.	20	80	µA
	Pad pull-down (when selected) at V_{IN} = 1.8V.	15	65	µA

V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot

Table 6: **V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot for HD I/O Banks**(1)

AC Voltage Overshoot	% of UI at –40°C to 100°C	AC Voltage Undershoot	% of UI at –40°C to 100°C
V_{CCO} + 0.30	100%	–0.30	100%
V_{CCO} + 0.35	100%	–0.35	90%
V_{CCO} + 0.40	100%	–0.40	78%
V_{CCO} + 0.45	100%	–0.45	40%
V_{CCO} + 0.50	100%	–0.50	24%
V_{CCO} + 0.55	100%	–0.55	18.0%
V_{CCO} + 0.60	100%	–0.60	13.0%
V_{CCO} + 0.65	100%	–0.65	10.8%
V_{CCO} + 0.70	92%	–0.70	9.0%
V_{CCO} + 0.75	92%	–0.75	7.0%
V_{CCO} + 0.80	92%	–0.80	6.0%
V_{CCO} + 0.85	92%	–0.85	5.0%
V_{CCO} + 0.90	92%	–0.90	4.0%
V_{CCO} + 0.95	92%	–0.95	2.5%

Notes:

1. A total of 200 mA per bank should not be exceeded.

Table 7: **V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot for HP I/O Banks**(1)(2)

AC Voltage Overshoot	% of UI at –40°C to 100°C	AC Voltage Undershoot	% of UI at –40°C to 100°C
V_{CCO} + 0.30	100%	–0.30	100%
V_{CCO} + 0.35	100%	–0.35	100%
V_{CCO} + 0.40	92%	–0.40	92%
V_{CCO} + 0.45	50%	–0.45	50%
V_{CCO} + 0.50	20%	–0.50	20%
V_{CCO} + 0.55	10%	–0.55	10%
V_{CCO} + 0.60	6%	–0.60	6%
V_{CCO} + 0.65	2%	–0.65	2%
V_{CCO} + 0.70	2%	–0.70	2%

Notes:

1. A total of 200 mA per bank should not be exceeded.
2. For UI smaller than 20 µs.

Table 9: **Typical Quiescent Supply Current[(1)][(2)][(3)][(4)]** ***(Cont'd)***

Symbol	Description	Device	Speed Grade and V_{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
I_{CCAUX_IOQ}	Quiescent V_{CCAUX_IO} supply current.	XCZU2	N/A	26	26	26	26	mA
		XCZU3	N/A	26	26	26	26	mA
		XCZU4	32	32	32	32	32	mA
		XCZU5	32	32	32	32	32	mA
		XCZU6	33	33	33	33	33	mA
		XCZU7	56	56	56	56	56	mA
		XCZU9	33	33	33	33	33	mA
		XCZU11	56	56	56	56	56	mA
		XCZU15	33	33	33	33	33	mA
		XCZU17	74	74	74	74	74	mA
		XCZU19	74	74	74	74	74	mA
$I_{CCBRAMQ}$	Quiescent V_{CCBRAM} supply current.	XCZU2	N/A	6	6	6	6	mA
		XCZU3	N/A	6	6	6	6	mA
		XCZU4	9	9	9	9	9	mA
		XCZU5	9	9	9	9	9	mA
		XCZU6	25	24	24	24	24	mA
		XCZU7	16	15	15	15	15	mA
		XCZU9	25	24	24	24	24	mA
		XCZU11	23	22	22	22	22	mA
		XCZU15	29	28	28	28	28	mA
		XCZU17	37	35	35	35	35	mA
		XCZU19	37	35	35	35	35	mA

Notes:

1. Typical values are specified at nominal voltage, 85°C junction temperatures (T_j) with single-ended SelectIO™ resources.
2. Typical values are for blank configured devices with no output current loads, no active input pull-up resistors, all I/O pins are 3-state and floating.
3. Use the Xilinx Power Estimator (XPE) spreadsheet tool (download at www.xilinx.com/power) to estimate static power consumption for conditions or supplies other than those specified.
4. Typical values depend upon your configuration. To accurately estimate all PS supply currents, use the interactive XPE spreadsheet tool.

Table 11: **Power Supply Ramp Time *(Cont'd)***

Symbol	Description	Min	Max	Units
T_{VCCO_PSDDR}	Ramp time from GND to 95% of V_{CCO_PSDDR}.	0.2	40	ms
$T_{VCC\_PSDDR\_PLL}$	Ramp time from GND to 95% of $V_{CC\_PSDDR\_PLL}$.	0.2	40	ms
T_{VCCO_PSIO}	Ramp time from GND to 95% of V_{CCO_PSIO}.	0.2	40	ms

DC Input and Output Levels

Values for V_{IL} and V_{IH} are recommended input voltages. Values for I_{OL} and I_{OH} are guaranteed over the recommended operating conditions at the V_{OL} and V_{OH} test points. Only selected standards are tested. These are chosen to ensure that all standards meet their specifications. The selected standards are tested at a minimum V_{CCO} with the respective V_{OL} and V_{OH} voltage levels shown. Other standards are sample tested.

PS I/O Levels

Table 12: **PS MIO and CONFIG DC Input and Output Levels**[1]

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
LVCMOS33	–0.300	0.800	2.000	V_{CCO_PSIO}	0.40	2.40	12	–12
LVCMOS25	–0.300	0.700	1.700	V_{CCO_PSIO} + 0.30	0.70	1.70	12	–12
LVCMOS18	–0.300	35% V_{CCO_PSIO}	65% V_{CCO_PSIO}	V_{CCO_PSIO} + 0.30	0.45	V_{CCO_PSIO} – 0.45	12	–12

Notes:

1. Tested according to relevant specifications.

Table 13: **PS DDR DC Input and Output Levels**[1]

DDR Standard	V_{IL}		V_{IH}		V_{OL}[2]	V_{OH}[2]	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
DDR4	0.000	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO_PSDDR}	0.8 x V_{CCO_PSDDR} – 0.150	0.8 x V_{CCO_PSDDR} + 0.150	10	–0.1
LPDDR4	0.000	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO_PSDDR}	0.3 x V_{CCO_PSDDR} – 0.150	0.3 x V_{CCO_PSDDR} + 0.150	0.1	–10
DDR3	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO_PSDDR}	0.5 x V_{CCO_PSDDR} – 0.175	0.5 x V_{CCO_PSDDR} + 0.175	8	–8
LPDDR3	0.000	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO_PSDDR}	0.5 x V_{CCO_PSDDR} – 0.150	0.5 x V_{CCO_PSDDR} + 0.150	8	–8
DDR3L	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO_PSDDR}	0.5 x V_{CCO_PSDDR} – 0.150	0.5 x V_{CCO_PSDDR} + 0.150	8	–8

Notes:

1. Tested according to relevant specifications.
2. DDR4 V_{OL}/V_{OH} specifications are only applicable for DQ/DQS pins.

Table 17: Differential SelectIO DC Input and Output Levels

I/O Standard	V_{ICM} (V)(1)			V_{ID}(V)(2)			V_{ILHS}(3)	V_{IHHS}(3)	V_{OCM}(V)(4)			V_{OD}(V)(5)		
	Min	Typ	Max	Min	Typ	Max	Min	Max	Min	Typ	Max	Min	Typ	Max
SUB_LVDS(8)	0.500	0.900	1.300	0.070	–	–	–	–	0.700	0.900	1.100	0.100	0.150	0.200
LVPECL	0.300	1.200	1.425	0.100	0.350	0.600	–	–	–	–	–	–	–	–
SLVS_400_18	0.070	0.200	0.330	0.140	–	0.450	–	–	–	–	–	–	–	–
SLVS_400_25	0.070	0.200	0.330	0.140	–	0.450	–	–	–	–	–	–	–	–
MIPI_DPHY_DCI_HS(9)	0.070	–	0.330	0.070	–	–	–0.040	0.460	0.150	0.200	0.250	0.140	0.200	0.270

Notes:

1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage ($Q - \overline{Q}$).
3. V_{IHHS} and V_{ILHS} are the single-ended input high and low voltages, respectively.
4. V_{OCM} is the output common mode voltage.
5. V_{OD} is the output differential voltage ($Q - \overline{Q}$).
6. LVDS_25 is specified in Table 23.
7. LVDS is specified in Table 24.
8. Only the SUB_LVDS receiver is supported in HD I/O banks.
9. High-speed option for MIPI_DPHY_DCI. The V_{ID} maximum is aligned with the standard's specification. A higher V_{ID} is acceptable as long as the V_{IN} specification is also met.

Table 18: Complementary Differential SelectIO DC Input and Output Levels for HD I/O Banks

I/O Standard	V_{ICM} (V)(1)			V_{ID} (V)(2)		V_{OL} (V)(3)	V_{OH} (V)(4)	I_{OL}	I_{OH}
	Min	Typ	Max	Min	Max	Max	Min	mA	mA
DIFF_HSTL_I	0.300	0.750	1.125	0.100	–	0.400	V_{CCO} – 0.400	8.0	–8.0
DIFF_HSTL_I_18	0.300	0.900	1.425	0.100	–	0.400	V_{CCO} – 0.400	8.0	–8.0
DIFF_HSUL_12	0.300	0.600	0.850	0.100	–	20% V_{CCO}	80% V_{CCO}	0.1	–0.1
DIFF_SSTL12	0.300	0.600	0.850	0.100	–	(V_{CCO}/2) – 0.150	(V_{CCO}/2) + 0.150	14.25	–14.25
DIFF_SSTL135	0.300	0.675	1.000	0.100	–	(V_{CCO}/2) – 0.150	(V_{CCO}/2) + 0.150	8.9	–8.9
DIFF_SSTL135_II	0.300	0.675	1.000	0.100	–	(V_{CCO}/2) – 0.150	(V_{CCO}/2) + 0.150	13.0	–13.0
DIFF_SSTL15	0.300	0.750	1.125	0.100	–	(V_{CCO}/2) – 0.175	(V_{CCO}/2) + 0.175	8.9	–8.9
DIFF_SSTL15_II	0.300	0.750	1.125	0.100	–	(V_{CCO}/2) – 0.175	(V_{CCO}/2) + 0.175	13.0	–13.0
DIFF_SSTL18_I	0.300	0.900	1.425	0.100	–	(V_{CCO}/2) – 0.470	(V_{CCO}/2) + 0.470	8.0	–8.0
DIFF_SSTL18_II	0.300	0.900	1.425	0.100	–	(V_{CCO}/2) – 0.600	(V_{CCO}/2) + 0.600	13.4	–13.4

Notes:

1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage.
3. V_{OL} is the single-ended low-output voltage.
4. V_{OH} is the single-ended high-output voltage.

Speed Grade Designations

Since individual family members are produced at different times, the migration from one category to another depends completely on the status of the fabrication process for each device. Table 26 correlates the current status of the Zynq UltraScale+ MPSoC on a per speed grade basis. See Table 3 for operating voltages listed by speed grade.

Table 26: **Speed Grade Designations by Device**

Device	Speed Grade, Temperature Ranges, and V_{CCINT} Operating Voltages		
	Advance	Preliminary	Production
XCZU2CG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU2EG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU3CG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU3EG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU4CG	-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU4EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU4EV	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU5CG	-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		

Table 26: **Speed Grade Designations by Device *(Cont'd)***

Device	Speed Grade, Temperature Ranges, and V_{CCINT} Operating Voltages		
	Advance	Preliminary	Production
XCZU5EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU5EV	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU6CG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU6EG	-3E (V_{CCINT} = 0.90V) -2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU7CG	-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU7EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU7EV	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU9CG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU9EG	-3E (V_{CCINT} = 0.90V) -2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)

Table 31: **PS NAND NV-DDR Synchronous Performance**

Memory Standard	Mode	Speed Grade			Units
		-3	-2	-1	
		Max	Max	Max	
NV-DDR(1)	5	200	200	200	Mb/s
	4	166.6	166.6	166.6	Mb/s
	3	133.3	133.3	133.3	Mb/s
	2	100	100	100	Mb/s
	1	66.6	66.6	66.6	Mb/s
	0	40	40	40	Mb/s

Notes:

1. The PS NAND memory controller interface for NV-DDR switching characteristics meets the requirements of the ONFI 3.1 specification.

Table 32: **PS NAND SDR Asynchronous Performance**

Memory Standard	Mode	Speed Grade			Units
		-3	-2	-1	
		Max	Max	Max	
SDR(1)(2)	5	50	50	50	Mb/s
	4	40	40	40	Mb/s
	3	33.3	33.3	33.3	Mb/s
	2	28.5	28.5	28.5	Mb/s
	1	20	20	20	Mb/s
	0	10	10	10	Mb/s

Notes:

1. The PS NAND memory controller interface for SDR switching characteristics meets the requirements of the ONFI 3.1 specification.
2. The NAND controller reference clock frequency maximum is 83 MHz.

Table 33: **PS-PL Interface Performance**

Symbol	Description	Min	Max	Units
$F_{EMIOGEMCLK}$	EMIO gigabit Ethernet controller maximum frequency.	–	125	MHz
$F_{EMIOSDCLK}$	EMIO SD controller maximum frequency.	–	25	MHz
$F_{EMIOSPICLK}$	EMIO SPI controller maximum frequency.	–	25	MHz
$F_{EMIOTRACECLK}$	EMIO trace controller maximum frequency.	–	125	MHz
$F_{FCIDMACLK}$	Flow control interface DMA maximum frequency.	–	333	MHz
F_{AXICLK}	Maximum AXI interface performance.	–	333	MHz
$F_{DPLIVEVIDEO}$	DisplayPort controller live video interface maximum frequency.	–	300	MHz

IOB High Performance (HP) Switching Characteristics

Table 76: **IOB High Performance (HP) Switching Characteristics**

I/O Standards	$T_{INBUF\_DELAY\_PAD\_I}$					$T_{OUTBUF\_DELAY\_O\_PAD}$					$T_{OUTBUF\_DELAY\_TD\_PAD}$					**Units**
	0.90V	**0.85V**		**0.72V**		**0.90V**	**0.85V**		**0.72V**		**0.90V**	**0.85V**		**0.72V**		
	-3	**-2**	**-1**	**-2**	**-1**	**-3**	**-2**	**-1**	**-2**	**-1**	**-3**	**-2**	**-1**	**-2**	**-1**	
DIFF_HSTL_I_12_F	0.394	0.394	0.402	0.394	0.402	0.423	0.423	0.443	0.423	0.443	0.553	0.553	0.582	0.553	0.582	ns
DIFF_HSTL_I_12_M	0.394	0.394	0.402	0.394	0.402	0.552	0.552	0.583	0.552	0.583	0.641	0.641	0.679	0.641	0.679	ns
DIFF_HSTL_I_12_S	0.394	0.394	0.402	0.394	0.402	0.752	0.752	0.800	0.752	0.800	0.813	0.813	0.868	0.813	0.868	ns
DIFF_HSTL_I_18_F	0.319	0.319	0.339	0.319	0.339	0.456	0.456	0.474	0.456	0.474	0.576	0.576	0.606	0.576	0.606	ns
DIFF_HSTL_I_18_M	0.319	0.319	0.339	0.319	0.339	0.570	0.570	0.603	0.570	0.603	0.653	0.653	0.692	0.653	0.692	ns
DIFF_HSTL_I_18_S	0.319	0.319	0.339	0.319	0.339	0.782	0.782	0.834	0.782	0.834	0.816	0.816	0.871	0.816	0.871	ns
DIFF_HSTL_I_DCI_12_F	0.394	0.394	0.402	0.394	0.402	0.406	0.406	0.429	0.406	0.429	0.534	0.534	0.564	0.534	0.564	ns
DIFF_HSTL_I_DCI_12_M	0.394	0.394	0.402	0.394	0.402	0.557	0.557	0.587	0.557	0.587	0.653	0.653	0.694	0.653	0.694	ns
DIFF_HSTL_I_DCI_12_S	0.394	0.394	0.402	0.394	0.402	0.755	0.755	0.806	0.755	0.806	0.842	0.842	0.907	0.842	0.907	ns
DIFF_HSTL_I_DCI_18_F	0.323	0.323	0.339	0.323	0.339	0.445	0.445	0.461	0.445	0.461	0.566	0.566	0.595	0.566	0.595	ns
DIFF_HSTL_I_DCI_18_M	0.323	0.323	0.339	0.323	0.339	0.555	0.555	0.586	0.555	0.586	0.643	0.643	0.684	0.643	0.684	ns
DIFF_HSTL_I_DCI_18_S	0.323	0.323	0.339	0.323	0.339	0.762	0.762	0.818	0.762	0.818	0.836	0.836	0.900	0.836	0.900	ns
DIFF_HSTL_I_DCI_F	0.397	0.397	0.417	0.397	0.417	0.431	0.431	0.445	0.431	0.445	0.555	0.555	0.575	0.555	0.575	ns
DIFF_HSTL_I_DCI_M	0.397	0.397	0.417	0.397	0.417	0.553	0.553	0.583	0.553	0.583	0.644	0.644	0.684	0.644	0.684	ns
DIFF_HSTL_I_DCI_S	0.397	0.397	0.417	0.397	0.417	0.767	0.767	0.823	0.767	0.823	0.848	0.848	0.912	0.848	0.912	ns
DIFF_HSTL_I_F	0.404	0.404	0.417	0.404	0.417	0.423	0.423	0.443	0.423	0.443	0.549	0.549	0.581	0.549	0.581	ns
DIFF_HSTL_I_M	0.404	0.404	0.417	0.404	0.417	0.555	0.555	0.586	0.555	0.586	0.640	0.640	0.677	0.640	0.677	ns
DIFF_HSTL_I_S	0.404	0.404	0.417	0.404	0.417	0.767	0.767	0.818	0.767	0.818	0.811	0.811	0.866	0.811	0.866	ns
DIFF_HSUL_12_DCI_F	0.381	0.381	0.400	0.381	0.400	0.425	0.425	0.443	0.425	0.443	0.558	0.558	0.586	0.558	0.586	ns
DIFF_HSUL_12_DCI_M	0.381	0.381	0.400	0.381	0.400	0.557	0.557	0.587	0.557	0.587	0.653	0.653	0.694	0.653	0.694	ns
DIFF_HSUL_12_DCI_S	0.381	0.381	0.400	0.381	0.400	0.737	0.737	0.787	0.737	0.787	0.822	0.822	0.885	0.822	0.885	ns
DIFF_HSUL_12_F	0.394	0.394	0.402	0.394	0.402	0.412	0.412	0.430	0.412	0.430	0.538	0.538	0.566	0.538	0.566	ns
DIFF_HSUL_12_M	0.394	0.394	0.402	0.394	0.402	0.552	0.552	0.583	0.552	0.583	0.641	0.641	0.679	0.641	0.679	ns
DIFF_HSUL_12_S	0.394	0.394	0.402	0.394	0.402	0.752	0.752	0.800	0.752	0.800	0.813	0.813	0.868	0.813	0.868	ns
DIFF_POD10_DCI_F	0.411	0.411	0.430	0.411	0.430	0.425	0.425	0.444	0.425	0.444	0.555	0.555	0.584	0.555	0.584	ns
DIFF_POD10_DCI_M	0.411	0.411	0.430	0.411	0.430	0.542	0.542	0.571	0.542	0.571	0.640	0.640	0.681	0.640	0.681	ns
DIFF_POD10_DCI_S	0.411	0.411	0.430	0.411	0.430	0.754	0.754	0.815	0.754	0.815	0.850	0.850	0.917	0.850	0.917	ns
DIFF_POD10_F	0.411	0.411	0.433	0.411	0.433	0.438	0.438	0.459	0.438	0.459	0.569	0.569	0.601	0.569	0.601	ns
DIFF_POD10_M	0.411	0.411	0.433	0.411	0.433	0.538	0.538	0.568	0.538	0.568	0.630	0.630	0.667	0.630	0.667	ns
DIFF_POD10_S	0.411	0.411	0.433	0.411	0.433	0.766	0.766	0.821	0.766	0.821	0.836	0.836	0.894	0.836	0.894	ns
DIFF_POD12_DCI_F	0.407	0.407	0.432	0.407	0.432	0.425	0.425	0.443	0.425	0.443	0.558	0.558	0.586	0.558	0.586	ns
DIFF_POD12_DCI_M	0.407	0.407	0.432	0.407	0.432	0.543	0.543	0.572	0.543	0.572	0.638	0.638	0.678	0.638	0.678	ns
DIFF_POD12_DCI_S	0.407	0.407	0.432	0.407	0.432	0.772	0.772	0.822	0.772	0.822	0.862	0.862	0.929	0.862	0.929	ns
DIFF_POD12_F	0.409	0.409	0.430	0.409	0.430	0.455	0.455	0.476	0.455	0.476	0.595	0.595	0.626	0.595	0.626	ns
DIFF_POD12_M	0.409	0.409	0.430	0.409	0.430	0.551	0.551	0.582	0.551	0.582	0.641	0.641	0.679	0.641	0.679	ns
DIFF_POD12_S	0.409	0.409	0.430	0.409	0.430	0.767	0.767	0.817	0.767	0.817	0.832	0.832	0.889	0.832	0.889	ns
DIFF_SSTL12_DCI_F	0.381	0.381	0.400	0.381	0.400	0.425	0.425	0.443	0.425	0.443	0.558	0.558	0.586	0.558	0.586	ns
DIFF_SSTL12_DCI_M	0.381	0.381	0.400	0.381	0.400	0.557	0.557	0.587	0.557	0.587	0.654	0.654	0.694	0.654	0.694	ns
DIFF_SSTL12_DCI_S	0.381	0.381	0.400	0.381	0.400	0.754	0.754	0.803	0.754	0.803	0.842	0.842	0.908	0.842	0.908	ns

Table 76: **IOB High Performance (HP) Switching Characteristics *(Cont'd)***

I/O Standards	$T_{INBUF\_DELAY\_PAD\_I}$					$T_{OUTBUF\_DELAY\_O\_PAD}$					$T_{OUTBUF\_DELAY\_TD\_PAD}$					Units
	0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
HSTL_I_DCI_S	0.393	0.393	0.415	0.393	0.415	0.766	0.766	0.821	0.766	0.821	0.847	0.847	0.912	0.847	0.912	ns
HSTL_I_F	0.378	0.378	0.399	0.378	0.399	0.423	0.423	0.443	0.423	0.443	0.549	0.549	0.581	0.549	0.581	ns
HSTL_I_M	0.378	0.378	0.399	0.378	0.399	0.554	0.554	0.585	0.554	0.585	0.640	0.640	0.677	0.640	0.677	ns
HSTL_I_S	0.378	0.378	0.399	0.378	0.399	0.766	0.766	0.816	0.766	0.816	0.811	0.811	0.866	0.811	0.866	ns
HSUL_12_DCI_F	0.378	0.378	0.399	0.378	0.399	0.425	0.425	0.443	0.425	0.443	0.558	0.558	0.586	0.558	0.586	ns
HSUL_12_DCI_M	0.378	0.378	0.399	0.378	0.399	0.556	0.556	0.586	0.556	0.586	0.654	0.654	0.694	0.654	0.694	ns
HSUL_12_DCI_S	0.378	0.378	0.399	0.378	0.399	0.736	0.736	0.784	0.736	0.784	0.821	0.821	0.886	0.821	0.886	ns
HSUL_12_F	0.378	0.378	0.399	0.378	0.399	0.412	0.412	0.430	0.412	0.430	0.538	0.538	0.566	0.538	0.566	ns
HSUL_12_M	0.378	0.378	0.399	0.378	0.399	0.551	0.551	0.582	0.551	0.582	0.642	0.642	0.679	0.642	0.679	ns
HSUL_12_S	0.378	0.378	0.399	0.378	0.399	0.750	0.750	0.799	0.750	0.799	0.813	0.813	0.868	0.813	0.868	ns
LVCMOS12_F_2	0.512	0.512	0.555	0.512	0.555	0.672	0.672	0.692	0.672	0.692	0.898	0.898	0.922	0.898	0.922	ns
LVCMOS12_F_4	0.512	0.512	0.555	0.512	0.555	0.504	0.504	0.521	0.504	0.521	0.664	0.664	0.693	0.664	0.693	ns
LVCMOS12_F_6	0.512	0.512	0.555	0.512	0.555	0.485	0.485	0.507	0.485	0.507	0.634	0.634	0.669	0.634	0.669	ns
LVCMOS12_F_8	0.512	0.512	0.555	0.512	0.555	0.465	0.465	0.489	0.465	0.489	0.611	0.611	0.666	0.611	0.666	ns
LVCMOS12_M_2	0.512	0.512	0.555	0.512	0.555	0.708	0.708	0.727	0.708	0.727	0.916	0.916	0.945	0.916	0.945	ns
LVCMOS12_M_4	0.512	0.512	0.555	0.512	0.555	0.550	0.550	0.573	0.550	0.573	0.664	0.664	0.690	0.664	0.690	ns
LVCMOS12_M_6	0.512	0.512	0.555	0.512	0.555	0.527	0.527	0.554	0.527	0.554	0.622	0.622	0.652	0.622	0.652	ns
LVCMOS12_M_8	0.512	0.512	0.555	0.512	0.555	0.540	0.540	0.571	0.540	0.571	0.614	0.614	0.649	0.614	0.649	ns
LVCMOS12_S_2	0.512	0.512	0.555	0.512	0.555	0.767	0.767	0.803	0.767	0.803	0.990	0.990	1.024	0.990	1.024	ns
LVCMOS12_S_4	0.512	0.512	0.555	0.512	0.555	0.666	0.666	0.704	0.666	0.704	0.803	0.803	0.848	0.803	0.848	ns
LVCMOS12_S_6	0.512	0.512	0.555	0.512	0.555	0.657	0.657	0.695	0.657	0.695	0.732	0.732	0.774	0.732	0.774	ns
LVCMOS12_S_8	0.512	0.512	0.555	0.512	0.555	0.708	0.708	0.761	0.708	0.761	0.745	0.745	0.790	0.745	0.790	ns
LVCMOS15_F_12	0.414	0.414	0.445	0.414	0.445	0.500	0.500	0.522	0.500	0.522	0.647	0.647	0.682	0.647	0.682	ns
LVCMOS15_F_2	0.414	0.414	0.445	0.414	0.445	0.702	0.702	0.722	0.702	0.722	0.919	0.919	0.940	0.919	0.940	ns
LVCMOS15_F_4	0.414	0.414	0.445	0.414	0.445	0.579	0.579	0.601	0.579	0.601	0.755	0.755	0.781	0.755	0.781	ns
LVCMOS15_F_6	0.414	0.414	0.445	0.414	0.445	0.547	0.547	0.569	0.547	0.569	0.711	0.711	0.742	0.711	0.742	ns
LVCMOS15_F_8	0.414	0.414	0.445	0.414	0.445	0.518	0.518	0.538	0.518	0.538	0.686	0.686	0.703	0.686	0.703	ns
LVCMOS15_M_12	0.414	0.414	0.445	0.414	0.445	0.607	0.607	0.644	0.607	0.644	0.637	0.637	0.676	0.637	0.676	ns
LVCMOS15_M_2	0.414	0.414	0.445	0.414	0.445	0.741	0.741	0.770	0.741	0.770	0.938	0.938	0.962	0.938	0.962	ns
LVCMOS15_M_4	0.414	0.414	0.445	0.414	0.445	0.625	0.625	0.651	0.625	0.651	0.754	0.754	0.786	0.754	0.786	ns
LVCMOS15_M_6	0.414	0.414	0.445	0.414	0.445	0.576	0.576	0.604	0.576	0.604	0.674	0.674	0.710	0.674	0.710	ns
LVCMOS15_M_8	0.414	0.414	0.445	0.414	0.445	0.568	0.568	0.601	0.568	0.601	0.639	0.639	0.681	0.639	0.681	ns
LVCMOS15_S_12	0.414	0.414	0.445	0.414	0.445	0.788	0.788	0.855	0.788	0.855	0.695	0.695	0.733	0.695	0.733	ns
LVCMOS15_S_2	0.414	0.414	0.445	0.414	0.445	0.829	0.829	0.864	0.829	0.864	1.039	1.039	1.079	1.039	1.079	ns
LVCMOS15_S_4	0.414	0.414	0.445	0.414	0.445	0.687	0.687	0.725	0.687	0.725	0.813	0.813	0.851	0.813	0.851	ns
LVCMOS15_S_6	0.414	0.414	0.445	0.414	0.445	0.671	0.671	0.710	0.671	0.710	0.726	0.726	0.763	0.726	0.763	ns
LVCMOS15_S_8	0.414	0.414	0.445	0.414	0.445	0.704	0.704	0.755	0.704	0.755	0.721	0.721	0.758	0.721	0.758	ns
LVCMOS18_F_12	0.418	0.418	0.445	0.418	0.445	0.573	0.573	0.601	0.573	0.601	0.731	0.731	0.769	0.731	0.769	ns
LVCMOS18_F_2	0.418	0.418	0.445	0.418	0.445	0.739	0.739	0.760	0.739	0.760	0.945	0.945	0.971	0.945	0.971	ns
LVCMOS18_F_4	0.418	0.418	0.445	0.418	0.445	0.609	0.609	0.630	0.609	0.630	0.778	0.778	0.802	0.778	0.802	ns
LVCMOS18_F_6	0.418	0.418	0.445	0.418	0.445	0.603	0.603	0.633	0.603	0.633	0.781	0.781	0.808	0.781	0.808	ns

Input Delay Measurement Methodology

Table 78 shows the test setup parameters used for measuring input delay.

Table 78: **Input Delay Measurement Methodology**

Description	I/O Standard Attribute	V_L(1)(2)	V_H(1)(2)	V_{MEAS} (1)(4)(6)	V_{REF} (1)(3)(5)
LVCMOS, 1.2V	LVCMOS12	0.1	1.1	0.6	–
LVCMOS, LVDCI, HSLVDCI, 1.5V	LVCMOS15, LVDCI_15, HSLVDCI_15	0.1	1.4	0.75	–
LVCMOS, LVDCI, HSLVDCI, 1.8V	LVCMOS18, LVDCI_18, HSLVDCI_18	0.1	1.7	0.9	–
LVCMOS, 2.5V	LVCMOS25	0.1	2.4	1.25	–
LVCMOS, 3.3V	LVCMOS33	0.1	3.2	1.65	–
LVTTL, 3.3V	LVTTL	0.1	3.2	1.65	–
HSTL (high-speed transceiver logic), class I, 1.2V	HSTL_I_12	V_{REF} – 0.25	V_{REF} + 0.25	V_{REF}	0.6
HSTL, class I, 1.5V	HSTL_I	V_{REF} – 0.325	V_{REF} + 0.325	V_{REF}	0.75
HSTL, class I, 1.8V	HSTL_I_18	V_{REF} – 0.4	V_{REF} + 0.4	V_{REF}	0.9
HSUL (high-speed unterminated logic), 1.2V	HSUL_12	V_{REF} – 0.25	V_{REF} + 0.25	V_{REF}	0.6
SSTL12 (stub series terminated logic), 1.2V	SSTL12	V_{REF} – 0.25	V_{REF} + 0.25	V_{REF}	0.6
SSTL135 and SSTL135 class II, 1.35V	SSTL135, SSTL135_II	V_{REF} – 0.2875	V_{REF} + 0.2875	V_{REF}	0.675
SSTL15 and SSTL15 class II, 1.5V	SSTL15, SSTL15_II	V_{REF} – 0.325	V_{REF} + 0.325	V_{REF}	0.75
SSTL18, class I and II, 1.8V	SSTL18_I, SSTL18_II	V_{REF} – 0.4	V_{REF} + 0.4	V_{REF}	0.9
POD10, 1.0V	POD10	V_{REF} – 0.2	V_{REF} + 0.2	V_{REF}	0.7
POD12, 1.2V	POD12	V_{REF} – 0.24	V_{REF} + 0.24	V_{REF}	0.84
DIFF_HSTL, class I, 1.2V	DIFF_HSTL_I_12	0.6 – 0.25	0.6 + 0.25	0(6)	–
DIFF_HSTL, class I, 1.5V	DIFF_HSTL_I	0.75 – 0.325	0.75 + 0.325	0(6)	–
DIFF_HSTL, class I, 1.8V	DIFF_HSTL_I_18	0.9 – 0.4	0.9 + 0.4	0(6)	–
DIFF_HSUL, 1.2V	DIFF_HSUL_12	0.6 – 0.25	0.6 + 0.25	0(6)	–
DIFF_SSTL, 1.2V	DIFF_SSTL12	0.6 – 0.25	0.6 + 0.25	0(6)	–
DIFF_SSTL135 and DIFF_SSTL135 class II, 1.35V	DIFF_SSTL135, DIFF_SSTL135_II	0.675 – 0.2875	0.675 + 0.2875	0(6)	–
DIFF_SSTL15 and DIFF_SSTL15 class II, 1.5V	DIFF_SSTL15, DIFF_SSTL15_II	0.75 – 0.325	0.75 + 0.325	0(6)	–
DIFF_SSTL18_I, DIFF_SSTL18_II, 1.8V	DIFF_SSTL18_I, DIFF_SSTL18_II	0.9 – 0.4	0.9 + 0.4	0(6)	–
DIFF_POD10, 1.0V	DIFF_POD10	0.5 – 0.2	0.5 + 0.2	0(6)	–
DIFF_POD12, 1.2V	DIFF_POD12	0.6 – 0.25	0.6 + 0.25	0(6)	–
LVDS (low-voltage differential signaling), 1.8V	LVDS	0.9 – 0.125	0.9 + 0.125	0(6)	–
LVDS_25, 2.5V	LVDS_25	1.25 – 0.125	1.25 + 0.125	0(6)	–

DSP48 Slice Switching Characteristics

Table 83: **DSP48 Slice Switching Characteristics**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
Maximum Frequency							
F_{MAX}	With all registers used.	891	775	645	644	600	MHz
F_{MAX_PATDET}	With pattern detector.	794	687	571	562	524	MHz
$F_{MAX\_MULT\_NOMREG}$	Two register multiply without MREG.	635	544	456	440	413	MHz
$F_{MAX\_MULT\_NOMREG\_PATDET}$	Two register multiply without MREG with pattern detect.	577	492	410	395	371	MHz
$F_{MAX\_PREADD\_NOADREG}$	Without ADREG.	655	565	468	453	423	MHz
$F_{MAX\_NOPIPELINEREG}$	Without pipeline registers (MREG, ADREG).	483	410	338	323	304	MHz
$F_{MAX\_NOPIPELINEREG\_PATDET}$	Without pipeline registers (MREG, ADREG) with pattern detect.	448	379	314	299	280	MHz

Clock Buffers and Networks

Table 84: **Clock Buffers Switching Characteristics**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
Global Clock Switching Characteristics (Including BUFGCTRL)							
F_{MAX}	Maximum frequency of a global clock tree (BUFG).	891	775	667	725	667	MHz
Global Clock Buffer with Input Divide Capability (BUFGCE_DIV)							
F_{MAX}	Maximum frequency of a global clock buffer with input divide capability (BUFGCE_DIV).	891	775	667	725	667	MHz
Global Clock Buffer with Clock Enable (BUFGCE)							
F_{MAX}	Maximum frequency of a global clock buffer with clock enable (BUFGCE).	891	775	667	725	667	MHz
Leaf Clock Buffer with Clock Enable (BUFCE_LEAF)							
F_{MAX}	Maximum frequency of a leaf clock buffer with clock enable (BUFCE_LEAF).	891	775	667	725	667	MHz
GTH or GTY Clock Buffer with Clock Enable and Clock Input Divide Capability (BUFG_GT)							
F_{MAX}	Maximum frequency of a serial transceiver clock buffer with clock enable and clock input divide capability.	512	512	512	512	512	MHz

Table 85: **MMCM Specification *(Cont'd)***

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
$MMCM\_F_{DPRCLK\_MAX}$	Maximum DRP clock frequency	250	250	250	250	250	MHz

Notes:

1. The MMCM does not filter typical spread-spectrum input clocks because they are usually far below the bandwidth filter frequencies.
2. The static offset is measured between any MMCM outputs with identical phase.
3. Values for this parameter are available in the Clocking Wizard.
4. Includes global clock buffer.
5. Calculated as F_{VCO}/128 assuming output duty cycle is 50%.

Table 91: **Global Clock Input Setup and Hold With MMCM**

Symbol	Description		Device	Speed Grade and V_{CCINT} Operating Voltages					Units
				0.90V	0.85V		0.72V		
				-3	-2	-1	-2	-1	
Input Setup and Hold Time Relative to Global Clock Input Signal using SSTL15 Standard.(1)(2)(3)									
$T_{PSMMCMCC\_ZU2}$	Global clock input and input flip-flop (or latch) with MMCM.	Setup	XCZU2	N/A	1.83	1.96	2.29	2.48	ns
$T_{PHMMCMCC\_ZU2}$		Hold			–0.19	–0.19	0.13	0.13	ns
$T_{PSMMCMCC\_ZU3}$		Setup	XCZU3	N/A	1.83	1.96	2.29	2.48	ns
$T_{PHMMCMCC\_ZU3}$		Hold			–0.19	–0.19	0.13	0.13	ns
$T_{PSMMCMCC\_ZU4}$		Setup	XCZU4	1.96	1.96	2.10	2.49	2.59	ns
$T_{PHMMCMCC\_ZU4}$		Hold		–0.12	–0.12	–0.12	0.27	0.48	ns
$T_{PSMMCMCC\_ZU5}$		Setup	XCZU5	1.96	1.96	2.10	2.49	2.59	ns
$T_{PHMMCMCC\_ZU5}$		Hold		–0.12	–0.12	–0.12	0.27	0.48	ns
$T_{PSMMCMCC\_ZU6}$		Setup	XCZU6	1.97	2.00	2.12	2.26	2.44	ns
$T_{PHMMCMCC\_ZU6}$		Hold		–0.11	–0.11	–0.11	0.16	0.18	ns
$T_{PSMMCMCC\_ZU7}$		Setup	XCZU7	1.91	1.91	2.02	2.45	2.70	ns
$T_{PHMMCMCC\_ZU7}$		Hold		–0.14	–0.14	–0.14	0.37	0.38	ns
$T_{PSMMCMCC\_ZU9}$		Setup	XCZU9	1.97	2.00	2.12	2.26	2.44	ns
$T_{PHMMCMCC\_ZU9}$		Hold		–0.11	–0.11	–0.11	0.16	0.18	ns
$T_{PSMMCMCC\_ZU11}$		Setup	XCZU11	2.08	2.08	2.23	2.59	2.75	ns
$T_{PHMMCMCC\_ZU11}$		Hold		–0.08	–0.08	0.04	0.35	0.74	ns
$T_{PSMMCMCC\_ZU15}$		Setup	XCZU15	1.96	1.99	2.12	2.26	2.44	ns
$T_{PHMMCMCC\_ZU15}$		Hold		–0.10	–0.10	–0.10	0.17	0.19	ns
$T_{PSMMCMCC\_ZU17}$		Setup	XCZU17	1.89	1.89	2.03	2.36	2.55	ns
$T_{PHMMCMCC\_ZU17}$		Hold		–0.16	–0.16	–0.16	0.31	0.34	ns
$T_{PSMMCMCC\_ZU19}$		Setup	XCZU19	1.89	1.89	2.03	2.36	2.55	ns
$T_{PHMMCMCC\_ZU19}$		Hold		–0.16	–0.16	–0.16	0.31	0.34	ns

Notes:

1. Setup and hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the global clock input signal using the slowest process, slowest temperature, and slowest voltage. Hold time is measured relative to the global clock input signal using the fastest process, fastest temperature, and fastest voltage.
2. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible I/O and CLB flip-flops are clocked by the global clock net.
3. Use IBIS to determine any duty-cycle distortion incurred using various standards.

Table 103: **GTH Transceiver Transmitter Switching Characteristics *(Cont'd)***

Symbol	Description	Condition	Min	Typ	Max	Units
$T_{J2.5}$	Total jitter(3)(4)	2.5 Gb/s(6)	–	–	0.20	UI
$D_{J2.5}$	Deterministic jitter(3)(4)		–	–	0.10	UI
$T_{J1.25}$	Total jitter(3)(4)	1.25 Gb/s(7)	–	–	0.15	UI
$D_{J1.25}$	Deterministic jitter(3)(4)		–	–	0.06	UI
T_{J500}	Total jitter(3)(4)	500 Mb/s(8)	–	–	0.10	UI
D_{J500}	Deterministic jitter(3)(4)		–	–	0.03	UI

Notes:

1. Using same REFCLK input with TX phase alignment enabled for up to four consecutive transmitters (one fully populated GTH Quad) at the maximum line rate.
2. Using QPLL_FBDIV = 40, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
3. Using CPLL_FBDIV = 2, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
4. All jitter values are based on a bit-error ratio of 10^{-12}.
5. CPLL frequency at 3.2 GHz and TXOUT_DIV = 2.
6. CPLL frequency at 2.5 GHz and TXOUT_DIV = 2.
7. CPLL frequency at 2.5 GHz and TXOUT_DIV = 4.
8. CPLL frequency at 2.0 GHz and TXOUT_DIV = 8.

Table 104: **GTH Transceiver Receiver Switching Characteristics**

Symbol	Description	Condition	Min	Typ	Max	Units
F_{GTHRX}	Serial data rate		0.500	–	F_{GTHMAX}	Gb/s
R_{XSST}	Receiver spread-spectrum tracking(1)	Modulated at 33 kHz	–5000	–	0	ppm
R_{XRL}	Run length (CID)		–	–	256	UI
$R_{XPPMTOL}$	Data/REFCLK PPM offset tolerance	Bit rates ≤ 6.6 Gb/s	–1250	–	1250	ppm
		Bit rates > 6.6 Gb/s and ≤ 8.0 Gb/s	–700	–	700	ppm
		Bit rates > 8.0 Gb/s	–200	–	200	ppm
SJ Jitter Tolerance(2)						
$J_{T\_SJ16.375}$	Sinusoidal jitter (QPLL)(3)	16.375 Gb/s	0.30	–	–	UI
$J_{T\_SJ15.0}$	Sinusoidal jitter (QPLL)(3)	15.0 Gb/s	0.30	–	–	UI
$J_{T\_SJ14.1}$	Sinusoidal jitter (QPLL)(3)	14.1 Gb/s	0.30	–	–	UI
$J_{T\_SJ13.1}$	Sinusoidal jitter (QPLL)(3)	13.1 Gb/s	0.30	–	–	UI
$J_{T\_SJ12.5}$	Sinusoidal jitter (QPLL)(3)	12.5 Gb/s	0.30	–	–	UI
$J_{T\_SJ11.3}$	Sinusoidal jitter (QPLL)(3)	11.3 Gb/s	0.30	–	–	UI
$J_{T\_SJ10.32\_QPLL}$	Sinusoidal jitter (QPLL)(3)	10.32 Gb/s	0.30	–	–	UI
$J_{T\_SJ10.32\_CPLL}$	Sinusoidal jitter (CPLL)(3)	10.32 Gb/s	0.30	–	–	UI
$J_{T\_SJ9.953\_QPLL}$	Sinusoidal jitter (QPLL)(3)	9.953 Gb/s	0.30	–	–	UI
$J_{T\_SJ9.953\_CPLL}$	Sinusoidal jitter (CPLL)(3)	9.953 Gb/s	0.30	–	–	UI
$J_{T\_SJ8.0}$	Sinusoidal jitter (QPLL)(3)	8.0 Gb/s	0.42	–	–	UI
$J_{T\_SJ6.6\_CPLL}$	Sinusoidal jitter (CPLL)(3)	6.6 Gb/s	0.44	–	–	UI
$J_{T\_SJ5.0}$	Sinusoidal jitter (CPLL)(3)	5.0 Gb/s	0.44	–	–	UI
$J_{T\_SJ4.25}$	Sinusoidal jitter (CPLL)(3)	4.25 Gb/s	0.44	–	–	UI
$J_{T\_SJ3.2}$	Sinusoidal jitter (CPLL)(3)	3.2 Gb/s(4)	0.45	–	–	UI

Table 104: **GTH Transceiver Receiver Switching Characteristics *(Cont'd)***

Symbol	Description	Condition	Min	Typ	Max	Units
$J_{T\_SJ2.5}$	Sinusoidal jitter (CPLL)(3)	2.5 Gb/s(5)	0.30	–	–	UI
$J_{T\_SJ1.25}$	Sinusoidal jitter (CPLL)(3)	1.25 Gb/s(6)	0.30	–	–	UI
J_{T_SJ500}	Sinusoidal jitter (CPLL)(3)	500 Mb/s(7)	0.30	–	–	UI
SJ Jitter Tolerance with Stressed Eye(2)						
$J_{T\_TJSE3.2}$	Total jitter with stressed eye(8)	3.2 Gb/s	0.70	–	–	UI
$J_{T\_TJSE6.6}$		6.6 Gb/s	0.70	–	–	UI
$J_{T\_SJSE3.2}$	Sinusoidal jitter with stressed eye(8)	3.2 Gb/s	0.10	–	–	UI
$J_{T\_SJSE6.6}$		6.6 Gb/s	0.10	–	–	UI

Notes:

1. Using RXOUT_DIV = 1, 2, and 4.
2. All jitter values are based on a bit error ratio of 10^{-12}.
3. The frequency of the injected sinusoidal jitter is 80 MHz.
4. CPLL frequency at 3.2 GHz and RXOUT_DIV = 2.
5. CPLL frequency at 2.5 GHz and RXOUT_DIV = 2.
6. CPLL frequency at 2.5 GHz and RXOUT_DIV = 4.
7. CPLL frequency at 2.0 GHz and RXOUT_DIV = 8.
8. Composite jitter with RX equalizer enabled. DFE disabled.

GTH Transceiver Electrical Compliance

The *UltraScale Architecture GTH Transceiver User Guide* (UG576) contains recommended use modes that ensure compliance for the protocols listed in Table 105. The transceiver wizard provides the recommended settings for those use cases and for protocol specific characteristics.

Table 110: **GTY Transceiver Dynamic Reconfiguration Port (DRP) Switching Characteristics**

Symbol	Description	All Speed Grades	Units
$F_{GTYDRPCLK}$	GTYDRPCLK maximum frequency.	250	MHz

Table 111: **GTY Transceiver Reference Clock Switching Characteristics**

Symbol	Description	Conditions	All Speed Grades			Units
			Min	Typ	Max	
F_{GCLK}	Reference clock frequency range.		60	–	820	MHz
T_{RCLK}	Reference clock rise time.	20% – 80%	–	200	–	ps
T_{FCLK}	Reference clock fall time.	80% – 20%	–	200	–	ps
T_{DCREF}	Reference clock duty cycle.	Transceiver PLL only	40	50	60	%

Table 112: **GTY Transceiver Reference Clock Oscillator Selection Phase Noise Mask**(1)

Symbol	Description	Offset Frequency	Min	Typ	Max	Units
$QPLL_{REFCLKMASK}$	QPLL0/QPLL1 reference clock select phase noise mask at REFCLK frequency = 156.25 MHz.	10 kHz	–	–	–112	dBc/Hz
		100 kHz	–	–	–128	
		1 MHz	–	–	–145	
	QPLL0/QPLL1 reference clock select phase noise mask at REFCLK frequency = 312.5 MHz.	10 kHz	–	–	–103	dBc/Hz
		100 kHz	–	–	–123	
		1 MHz	–	–	–143	
	QPLL0/QPLL1 reference clock select phase noise mask at REFCLK frequency =625 MHz.	10 kHz	–	–	–98	dBc/Hz
		100 kHz	–	–	–117	
		1 MHz	–	–	–140	
$CPLL_{REFCLKMASK}$	CPLL reference clock select phase noise mask at REFCLK frequency = 156.25 MHz.	10 kHz	–	–	–112	dBc/Hz
		100 kHz	–	–	–128	
		1 MHz	–	–	–145	
		50 MHz	–	–	–145	
	CPLL reference clock select phase noise mask at REFCLK frequency = 312.5 MHz.	10 kHz	–	–	–103	dBc/Hz
		100 kHz	–	–	–123	
		1 MHz	–	–	–143	
		50 MHz	–	–	–145	
	CPLL reference clock select phase noise mask at REFCLK frequency = 625 MHz.	10 kHz	–	–	–98	dBc/Hz
		100 kHz	–	–	–117	
		1 MHz	–	–	–140	
		50 MHz	–	–	–144	

Notes:

1. For reference clock frequencies not in this table, use the phase-noise mask for the nearest reference clock frequency.
2. This reference clock phase-noise mask is superseded by any reference clock phase-noise mask that is specified in a supported protocol, e.g., PCIe.

Integrated Interface Block for Interlaken

More information and documentation on solutions using the integrated interface block for Interlaken can be found at UltraScale+ Interlaken. The *UltraScale Architecture and Product Overview* (DS890) lists how many blocks are in each Zynq UltraScale+ MPSoC. This section describes the following Interlaken configurations.

- 12 x 12.5 Gb/s protocol and lane logic mode (Table 118).
- 6 x 25.78125 Gb/s and 6 x 28.21 Gb/s protocol and lane logic mode (Table 119).
- 12 x 25.78125 Gb/s lane logic only mode (Table 120).

Zynq UltraScale+ MPSoCs in the SFVB784, FFVA676, and FFVA1156 packages are only supported using the 12 x 12.5 Gb/s Interlaken configuration. See Table 109 for the F_{GTYMAX} description.

Table 118: **Maximum Performance for Interlaken 12 x 12.5 Gb/s Protocol and Lane Logic Mode Designs**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages										Units
		0.90V		0.85V				0.72V				
		-3		-2		-1		-2		-1		
$F_{RX\_SERDES\_CLK}$	Receive serializer/ deserializer clock	195.32		195.32		195.32		195.32		195.32		MHz
$F_{TX\_SERDES\_CLK}$	Transmit serializer/ deserializer clock	195.32		195.32		195.32		195.32		195.32		MHz
F_{DRP_CLK}	Dynamic reconfiguration port clock	250.00		250.00		250.00		250.00		250.00		MHz
		Min(1)	Max	Min(1)	Max	Min(1)	Max	Min(1)	Max	Min(1)	Max	
F_{CORE_CLK}	Interlaken core clock	300.00	322.27	300.00	322.27	300.00	322.27	300.00	322.27	300.00	322.27	MHz
F_{LBUS_CLK}	Interlaken local bus clock	300.00	322.27	300.00	322.27	300.00	322.27	300.00	322.27	300.00	322.27	MHz

Notes:

1. These are the minimum clock frequencies at the maximum lane performance.

Integrated Interface Block for 100G Ethernet MAC and PCS

More information and documentation on solutions using the integrated 100 Gb/s Ethernet block can be found at UltraScale+ Integrated 100G Ethernet MAC/PCS. The *UltraScale Architecture and Product Overview* (DS890) lists how many blocks are in each Zynq UltraScale+ MPSoC.

Table 121: **Maximum Performance for 100G Ethernet Designs**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2(1)	-1	-2	-1(2)	
F_{TX_CLK}	Transmit clock	390.625	390.625	322.223	322.223	322.223	MHz
F_{RX_CLK}	Receive clock	390.625	390.625	322.223	322.223	322.223	MHz
$F_{RX\_SERDES\_CLK}$	Receive serializer/deserializer clock	390.625	390.625	322.223	322.223	322.223	MHz
F_{DRP_CLK}	Dynamic reconfiguration port clock	250.00	250.00	250.00	250.00	250.00	MHz

Notes:

1. The maximum clock frequency of 390.625 MHz only applies to the CAUI-10 interface. The maximum clock frequency for the CAUI-4 interface is 322.223 MHz.
2. The CAUI-4 interface is not supported by -1L speed grade devices where V_{CCINT}=0.72V.

Integrated Interface Block for PCI Express Designs

More information and documentation on solutions for PCI Express designs can be found at PCI Express. The *UltraScale Architecture and Product Overview* (DS890) lists the Zynq UltraScale+ MPSoCs that include this block.

Table 122: **Maximum Performance for PCI Express Designs(1)(2)**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
$F_{PIPECLK}$	Pipe clock maximum frequency.	250.00	250.00	250.00	250.00	250.00	MHz
$F_{CORECLK}$	Core clock maximum frequency.	500.00	500.00	500.00	250.00	250.00	MHz
F_{DRPCLK}	DRP clock maximum frequency.	250.00	250.00	250.00	250.00	250.00	MHz
$F_{MCAPCLK}$	MCAP clock maximum frequency.	125.00	125.00	125.00	125.00	125.00	MHz

Notes:

1. PCI Express Gen4 operation is supported for x1, x2, x4, and x8 widths.
2. PCI Express Gen4 operation is supported in -3E, -2E, and -2I speed grades.